



**FDMB3800N**

## Dual N-Channel PowerTrench® MOSFET

**30V, 4.8A, 40mΩ**

## Features

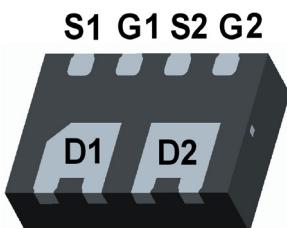
- Max  $r_{DS(on)}$  = 40mΩ at  $V_{GS}$  = 10V,  $I_D$  = 4.8A
- Max  $r_{DS(on)}$  = 51mΩ at  $V_{GS}$  = 4.5V,  $I_D$  = 4.3A
- Fast switching speed
- Low gate Charge
- High performance trench technology for extremely low  $r_{DS(on)}$
- High power and current handling capability.
- RoHS Compliant



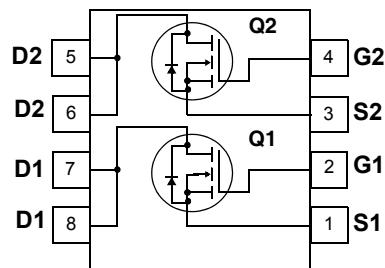
## General Description

These N-Channel Logic Level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.



## MicroFET 3X1.9



## MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	30	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous	$T_A = 25^\circ\text{C}$	A
	-Pulsed		
$P_D$	Power Dissipation	$T_A = 25^\circ\text{C}$	W
	Power Dissipation	$T_A = 25^\circ\text{C}$	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

## Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	80	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	165	

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
3800	FDMB3800N	MicroFET3X1.9	7"	8mm	3000 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

**Off Characteristics**

$\text{BV}_{\text{DSS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	30			V
$\frac{\Delta \text{BV}_{\text{DSS}}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		24		$\text{mV}/^\circ\text{C}$
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$		1	10	$\mu\text{A}$
$I_{\text{GSS}}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			$\pm 100$	nA

**On Characteristics**

$V_{GS(\text{th})}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	1	1.9	3	V
$\frac{\Delta V_{GS(\text{th})}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-4		$\text{mV}/^\circ\text{C}$
$r_{DS(\text{on})}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 4.8\text{A}$		32	40	
		$V_{GS} = 4.5\text{V}, I_D = 4.3\text{A}$		41	51	$\text{m}\Omega$
		$V_{GS} = 10\text{V}, I_D = 4.8\text{A}, T_J = 125^\circ\text{C}$		43	61	
$g_{\text{fs}}$	Forward Transconductance	$V_{DS} = 5\text{V}, I_D = 4.8\text{A}$		14		S

**Dynamic Characteristics**

$C_{\text{iss}}$	Input Capacitance	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		350	465	pF
$C_{\text{oss}}$	Output Capacitance			90	120	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance			40	60	pF
$R_g$	Gate Resistance	$f = 1\text{MHz}$		3		$\Omega$

**Switching Characteristics**

$t_{d(\text{on})}$	Turn-On Delay Time	$V_{DD} = 15\text{V}, I_D = 1\text{A}$ $V_{GS} = 10\text{V}, R_{\text{GEN}} = 6\Omega$		8	16	ns
$t_r$	Rise Time			5	10	ns
$t_{d(\text{off})}$	Turn-Off Delay Time			21	34	ns
$t_f$	Fall Time			2	10	ns
$Q_{g(\text{TOT})}$	Total Gate Charge at 5V	$V_{GS} = 0\text{V to } 5\text{V}$ $V_{DD} = 15\text{V}$ $I_D = 7.5\text{A}$		4	5.6	nC
$Q_{gs}$	Gate to Source Gate Charge			1.0		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			1.5		nC

**Drain-Source Diode Characteristics**

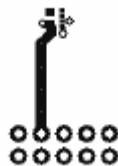
$I_S$	Maximum Continuous Drain - Source Diode Forward Current			1.25		A
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 1.25\text{A}$ (Note 2)		0.8	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F = 4.8\text{A}, di/dt = 100\text{A}/\mu\text{s}$		17		ns
$Q_{rr}$	Reverse Recovery Charge				7	

**Notes:**

1:  $R_{\text{QJA}}$  is determined with the device mounted on a  $1\text{in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5$  in. board of FR-4 material.  $R_{\text{QJC}}$  is guaranteed by design while  $R_{\text{QCA}}$  is determined by the user's board design.



a.  $80^\circ\text{C}/\text{W}$  when mounted on a  $1\text{in}^2$  pad of 2 oz copper



b.  $165^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty cycle  $< 2.0\%$ .

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

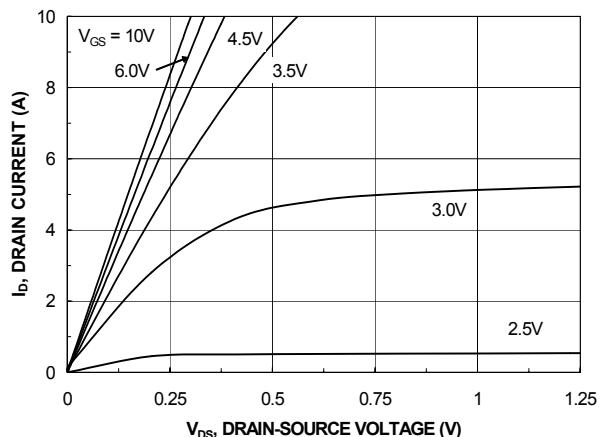


Figure 1. On Region Characteristics

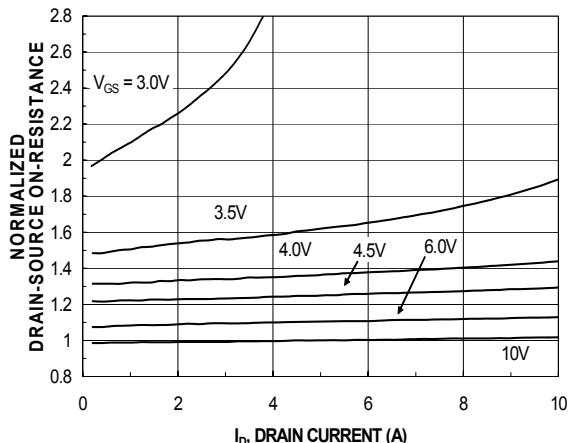


Figure 2. Normalized On -Resistance vs Drain Current and Gate Voltage

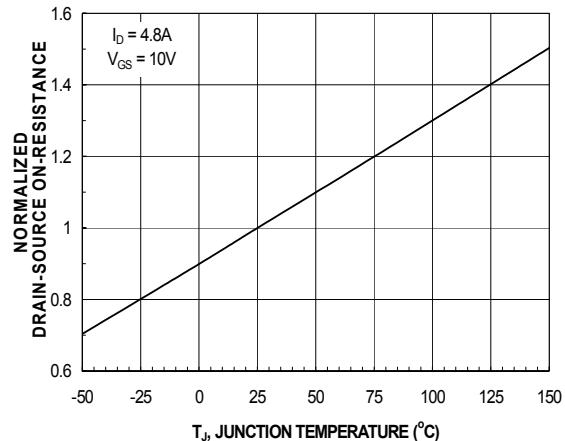


Figure 3. Normalized On -Resistance vs Junction Temperature

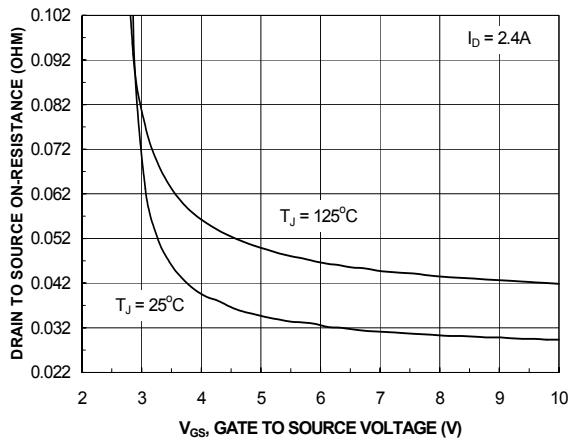


Figure 4. On-Resistance vs Gate to Source Voltage

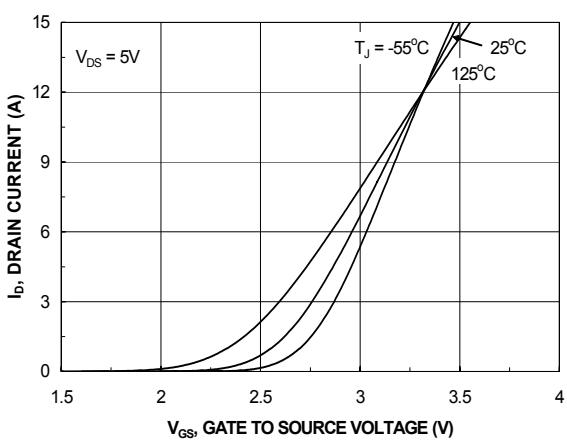


Figure 5. Transfer Characteristics

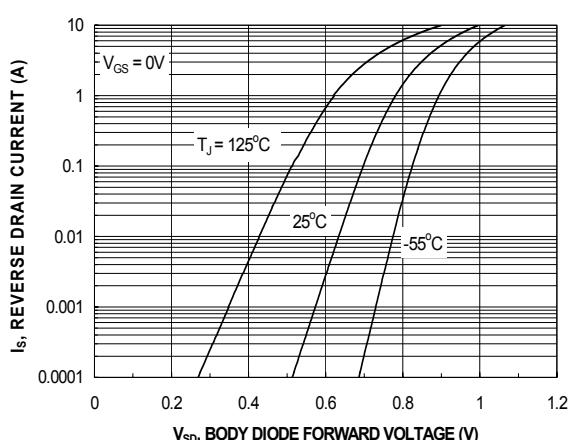


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

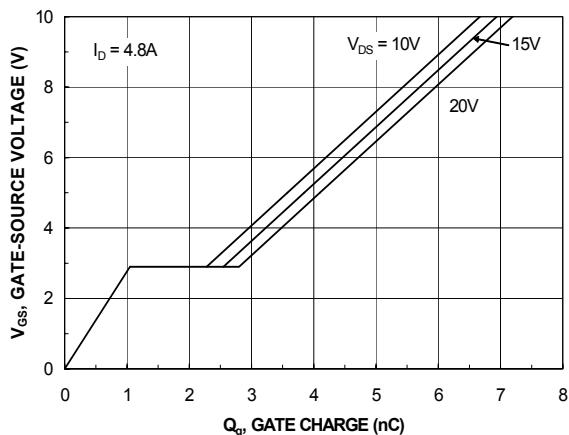


Figure 7. Gate Charge Characteristics

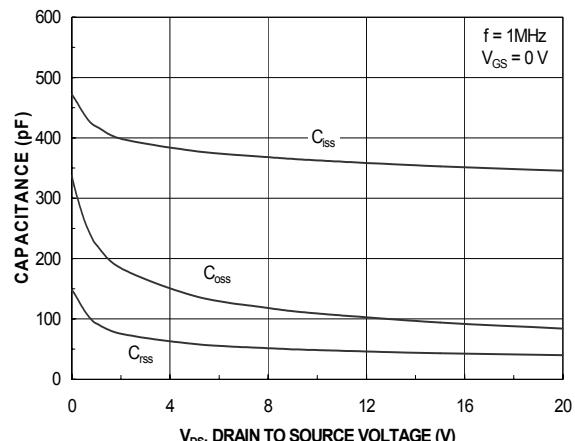


Figure 8. Capacitance vs Drain to Source Voltage

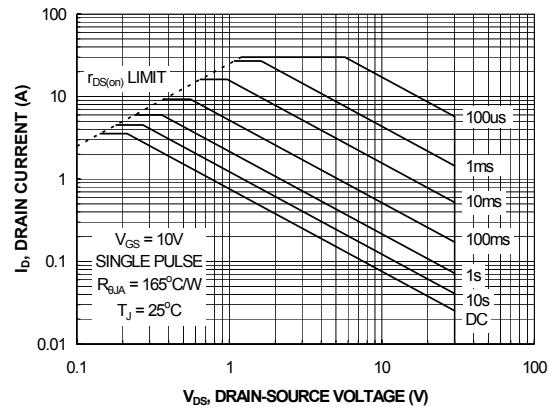


Figure 9. Forward Bias Safe Operating Area

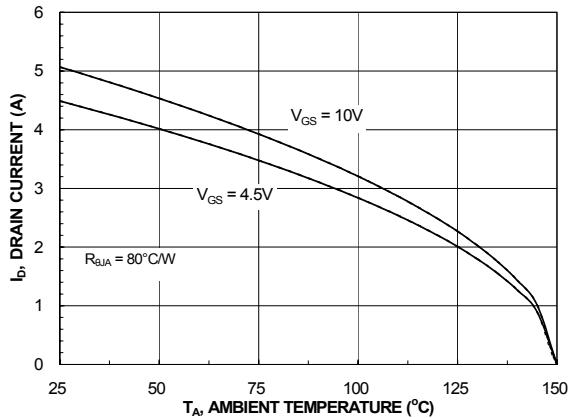


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

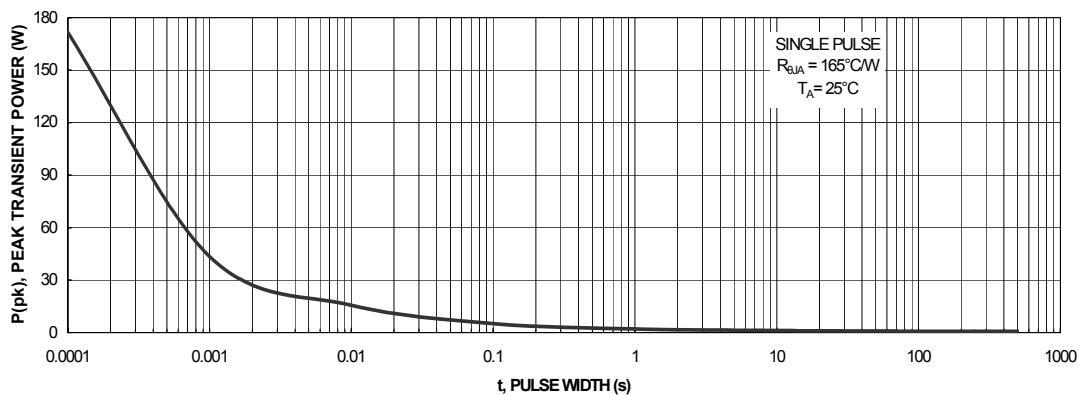


Figure 11. Single Pulse Maximum Power Dissipation

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

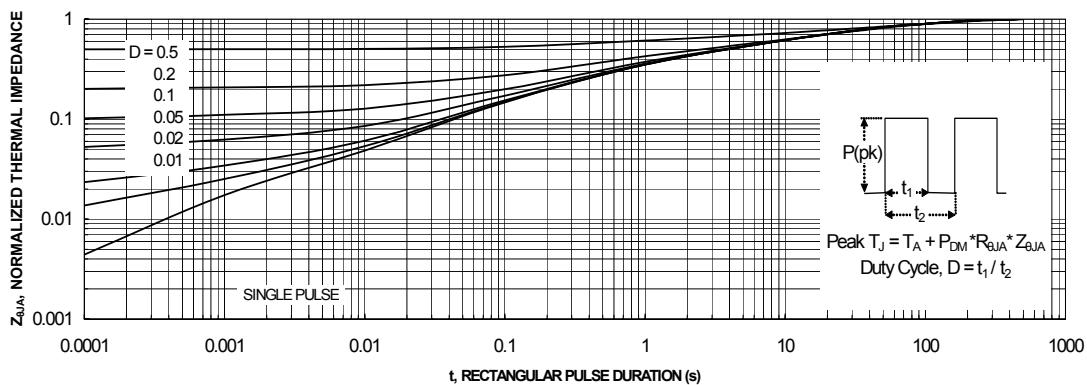
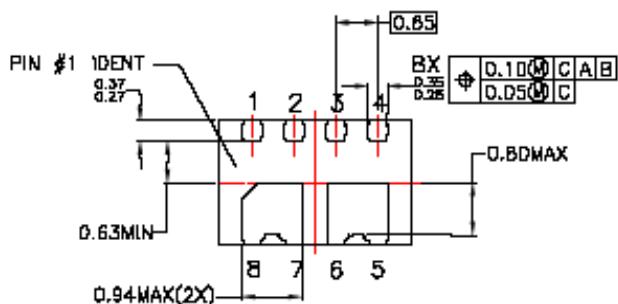
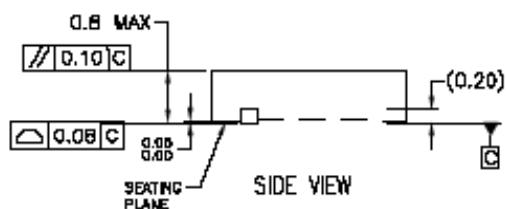
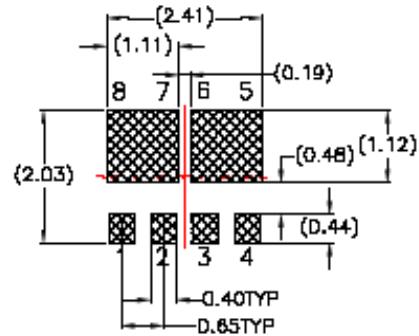
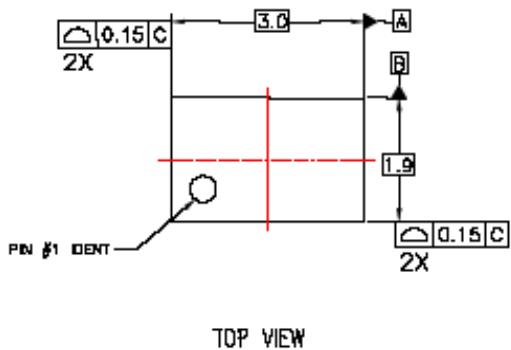


Figure 12. Transient Thermal Response Curve

Dimensional Outline and Pad Layout



## TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACEx™	FACT Quiet Series™	OCX™	SILENT SWITCHER®	UniFET™
ActiveArray™	GlobalOptoisolator™	OCXPro™	SMART START™	UltraFET®
Bottomless™	GTO™	OPTOLOGIC®	SPM™	VCX™
Build it Now™	HiSeC™	OPTOPLANAR™	Stealth™	Wire™
CoolFET™	I <sup>2</sup> C™	PACMAN™	SuperFET™	
CROSSVOLT™	i-Lo™	POP™	SuperSOT™-3	
DOME™	ImpliedDisconnect™	Power247™	SuperSOT™-6	
EcoSPARK™	IntelliMAX™	PowerEdge™	SuperSOT™-8	
E <sup>2</sup> CMOS™	ISOPLANAR™	PowerSaver™	SyncFET™	
EnSigna™	LittleFET™	PowerTrench®	TCM™	
FACT™	MICROCOUPLER™	QFET®	TinyBoost™	
FAST®	MicroFET™	QST™	TinyBuck™	
FASTR™	MicroPak™	QT Optoelectronics™	TinyPWM™	
FPS™	MICROWIRE™	Quiet Series™	TinyPower™	
FRFET™	MSX™	RapidConfigure™	TinyLogic®	
	MSXPro™	RapidConnect™	TINYOPTO™	
Across the board. Around the world.™		µSerDes™	TruTranslation™	
The Power Franchise®		ScalarPump™	UHC™	
Programmable Active Droop™				

## DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

## LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.